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Vishay Semiconductors

650 V Power SiC Merged PIN Schottky Diode, 8 A



LINKS TO ADDITIONAL RESOURCES







PRIMARY CHARACTERISTICS				
I _{F(AV)}	8 A			
V _R	650 V			
V _F at I _F at 150 °C	1.7 V			
T _J max.	175 °C			
I _R at V _R at 175 °C	5 μΑ			
Q _C (V _R = 400 V)	23 nC			
Package	2L TO-220AC			
Circuit configuration	Single			

FEATURES

 Majority carrier diode using Schottky technology on SiC wide band gap material



Positive V_F temperature coefficient for easy paralleling

- · Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 1A whisker test
- Solder Bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

MECHANICAL DATA

Case: 2L TO-220AC

Molding compound meets UL 94 V-0 flammability rating

Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

Mounting torque: 10 in-lbs maximum

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C unless otherwise specified)				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		650	V
Average rectified forward current	I _{F(AV)}	$T_C = 126 ^{\circ}C (DC)$	8	Α
DC blocking voltage	V_{DC}		650	V
Repetitive peak surge current	I _{FRM}	T_C = 25 °C, f = 50 Hz, square wave, DC = 25 %	29.5	
Manager 192	I _{FSM}	$T_C = 25$ °C, $t_p = 10$ ms, half sine wave	57	Α
Non-repetitive peak forward surge current		$T_C = 110 ^{\circ}\text{C}$, $t_p = 10 \text{ms}$, half sine wave	49	İ
Danier diagination	P _{tot} (1)	T _C = 25 °C	54	w
Power dissipation		T _C = 110 °C	23] vv
I ² t value	∫i ² dt	$T_C = 25 ^{\circ}C$	16	42-
		T _C = 110 °C	12	A ² s
Operating junction and storage temperatures	T _J ⁽²⁾ , T _{Stg}		-55 to +175	°C

Notes

⁽¹⁾ Based on maximum Rth

 $^{^{(2)}}$ The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_J < 1/R_{\theta JA}$



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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
		I _F = 8 A	-	1.50	1.80	
Forward voltage	V _F	I _F = 8 A, T _J = 150 °C	-	1.7	2.1	V
		I _F = 8 A, T _J = 175 °C	-	1.8	-	
		$V_R = V_R$ rated	-	-	45	
Reverse leakage current	I _R	V _R = V _R rated, T _J = 150 °C	-	=.	100	μA
		V _R = V _R rated, T _J = 175 °C	-	5	-	
Total capacitance	С	V _R = 1 V, f = 1 MHz	-	355	-	nE.
		V _R = 400 V, f = 1 MHz	-	37	-	pF
Total capacitive charge	Q _C	V _R = 400 V, f = 1 MHz	-	23	-	nC

THERMAL - MECHANICAL SPECIFICATIONS (T _A = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction-to-case	R _{thJC}		-	2	2.8	°C/W
Marking device	C08ETC		T07T			

1000

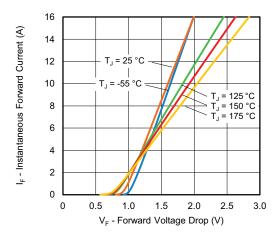
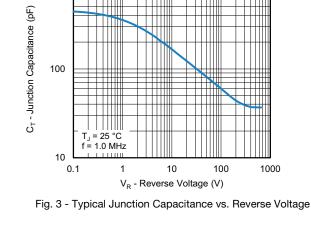


Fig. 1 - Typical Forward Voltage Drop Characteristics



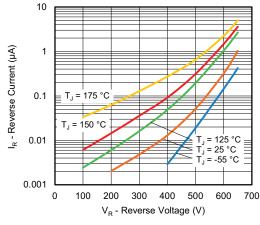


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

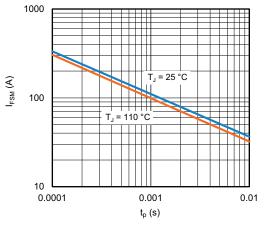


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

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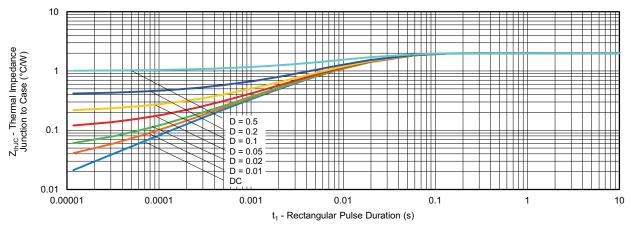


Fig. 5 - Typical Thermal Impedance Z_{thJC} Characteristics

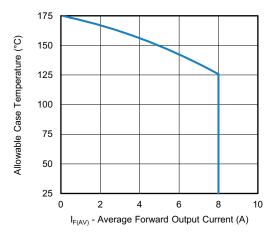


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

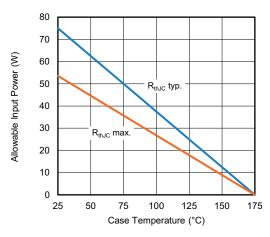


Fig. 7 - Forward Power Loss Characteristics

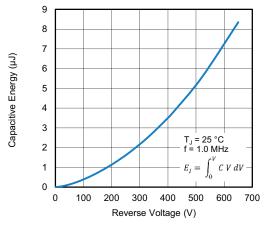


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

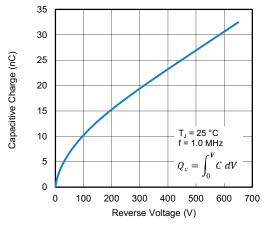


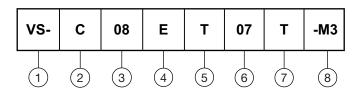
Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage



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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - C = SiC diode

3 - Current rating (08 = 8 A)

E = single diodePackage TO-220

6 - Voltage rating: (07 = 650 V)

7 - T = true 2 pin

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION				
PREFERRED P/N	BASE QUANTITY	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-C08ET07T-M3	50/tube	1000	Antistatic plastic tubes	

LINKS TO RELATED DOCUMENTS			
Dimensions <u>www.vishay.com/doc?96069</u>			
Part marking information	www.vishay.com/doc?95391		
SPICE model	www.vishay.com/doc?96831		



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